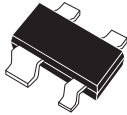


BAS56

DUAL HIGH CURRENT SWITCHING DIODE



SOT-143 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAS56 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package with isolated dual diodes, designed for high current, high speed switching applications.

Marking code is L51.

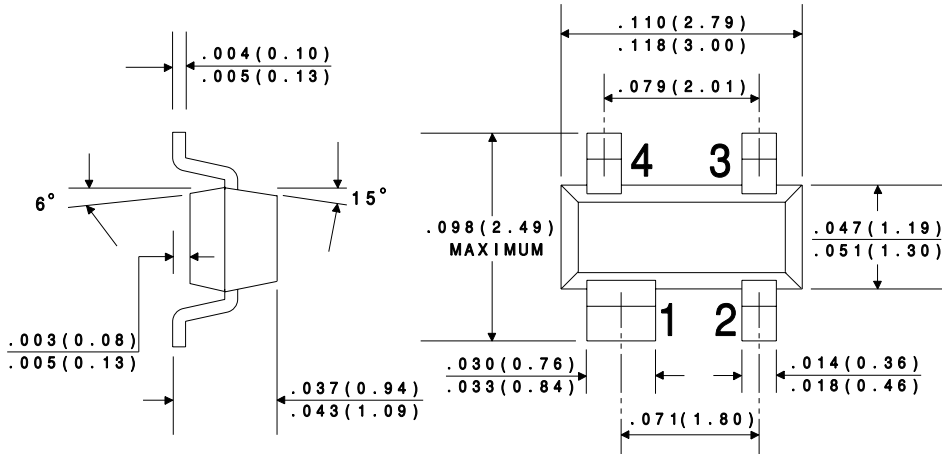
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V _R	60	V
Peak Repetitive Reverse Voltage	V _{RRM}	60	V
Continuous Forward Current	I _F	200	mA
Peak Repetitive Forward Current	I _{FRM}	600	mA
Forward Surge Current, tp=1 μsec.	I _{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I _{FSM}	1000	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =60V		100	nA
I _R	V _R =60V, T _A =150°C		100	μA
I _R	V _R =75V		10	μA
V _F	I _F =10mA		0.75	V
V _F	I _F =200mA		1.00	V
V _F	I _F =500mA		1.25	V
C _T	V _R =0, f=1 MHz		2.5	pF
t _{rr}	I _F =I _R =400mA, R _L =100Ω, Rec. to 40mA		6.0	ns
Q _s	I _F =10mA, V _R =5.0V, R _L =500Ω		50	pC
V _{FR}	I _F =400mA, t _r =30ns		1.2	V
V _{FR}	I _F =400mA, t _r =100ns		1.5	V

All dimensions in inches (mm).



LEAD CODE:

- 1) ANODE 1
- 2) ANODE 2
- 3) CATHODE 2
- 4) CATHODE 1